TO-126 Plastic-Encapsulate Transistors

AV772 TRANSISTOR（ PNP ）

FEATURES

Power dissipation

P_{CM} : 1.25 W（Tamb=25℃）

Collector current

I_{CM} : -3 A

Collector-base voltage

$V_{(BR)CBO}$: - 40 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

TO-126

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -100μA， I_E=0	-40		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= -10 mA， I_B=0	-30		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -100μA， I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40 V， I_E=0		-1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -30 V， I_B=0		-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -6 V， I_C=0		-1	μA
DC current gain	$H_{FE(1)}$	V_{CE}= -2 V, I_C= -1A	60	400	
	$H_{FE(2)}$	V_{CE}= -2 V, I_C= -100mA	32		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -2A, I_B= -0.2 A		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= -2A, I_B= -0.2 A		-2	V
Transition frequency	f_T	V_{CE}= -5V , Ic=-0.1A f =10MHz	50		MHz

CLASSIFICATION OF HFE(1)

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

TYPICAL PERFORMANCE CHARACTERISTICS

Fig.1 Static characteristics

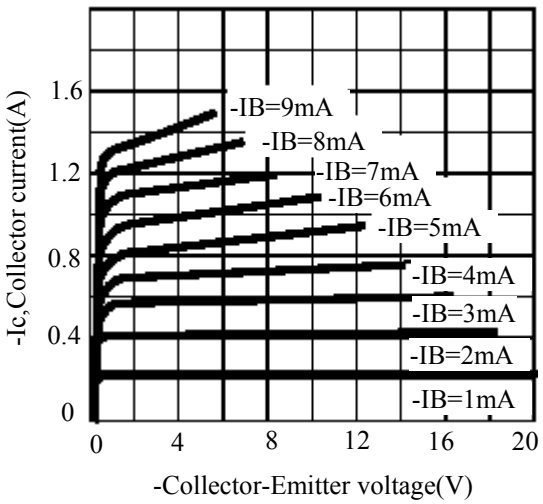

Fig.2 Derating curve of safe operating areas

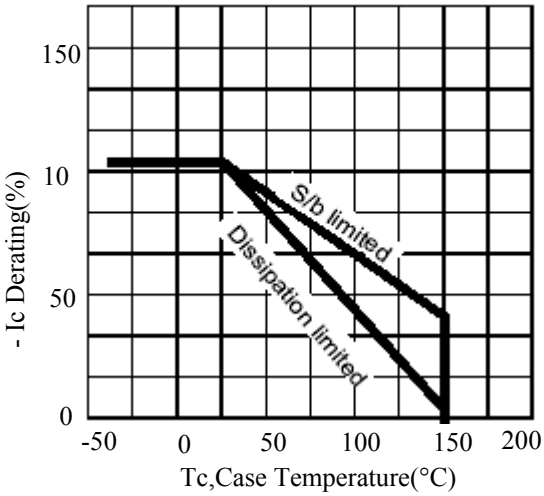

Fig.3 Power Derating

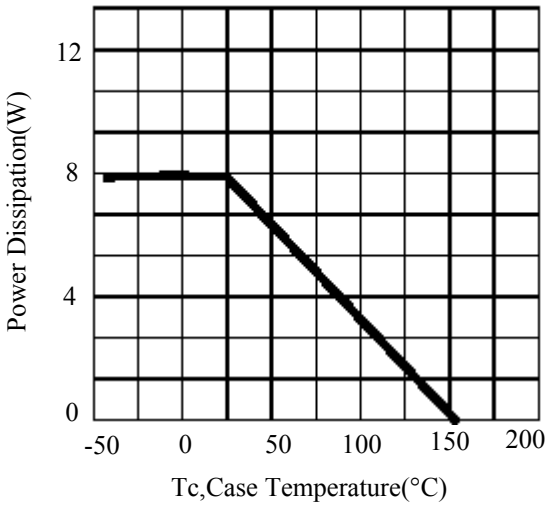

Fig.4 Collector Output capacitance

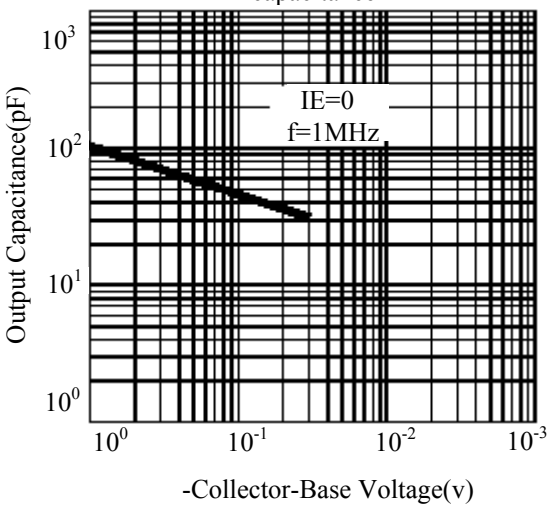

Fig.5 Current gain-bandwidth product

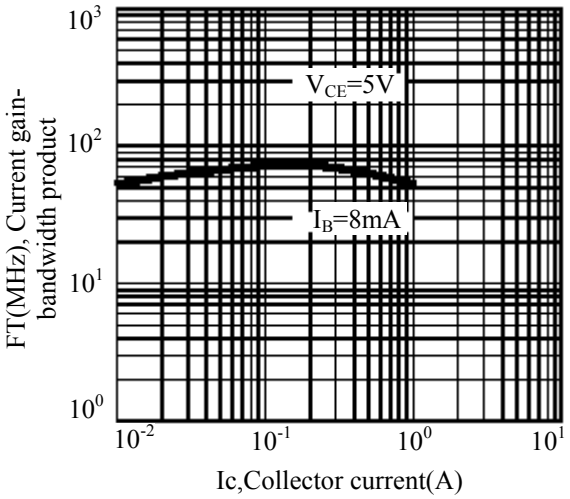

Fig.6 Safe operating area

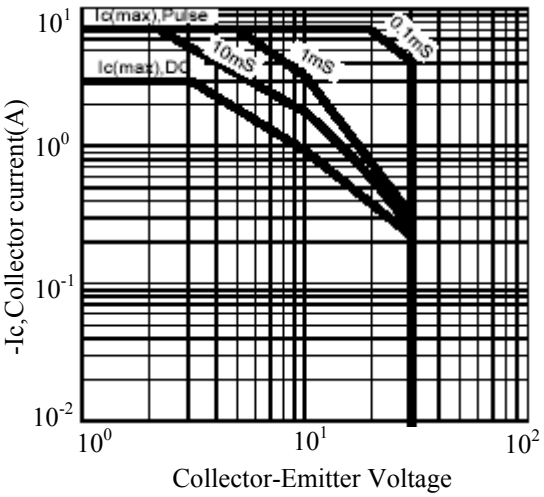

Fig.7 DC current gain

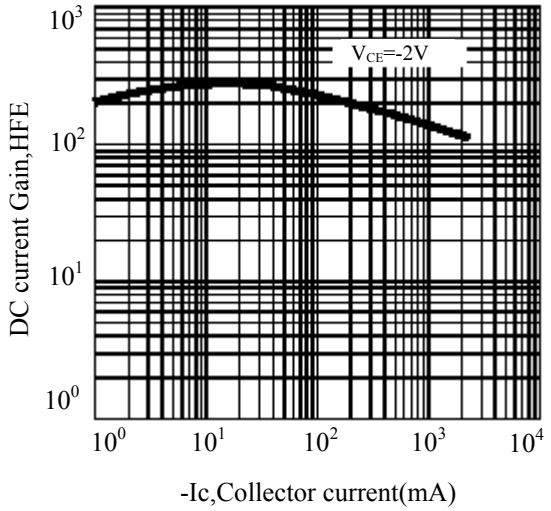

Fig.8 Saturation